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Customer Number

Patent  
Case No.: 58434US002

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

First Named Inventor: MUYRES, DAWN V.

Application No.: 10/642919 Confirmation No.: 3648

Filed: August 18, 2003

Title: METHOD FOR SEALING THIN FILM TRANSISTORS

**RESPONSE TO RESTRICTION REQUIREMENT**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**CERTIFICATE OF MAILING OR TRANSMISSION [37 CFR § 1.8(a)]**

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Date

*Hylys H. Freelke*  
Signed by: Hylys H. Freelke

Dear Sir:

This is in response to the Office Action dated December 31, 2007. Claims 1 - 30 are pending.

**Restriction Requirement**

Claims 1 - 30 were restricted under 35 U.S.C. § 121 as follows:

- I. Claims 1 - 11 and 13 - 28, said to be drawn to a method of producing a thin film transistor, classified in Class 438, subclass 99;
- II. Claims 12 and 29, said to be drawn to the method of Invention I in combination with a surface treatment layer, classified in Class 438, subclass 99; and
- II. Claim 30, said to be drawn to a thin film transistor, classified in class 257, subclass 40.

In response, Applicants hereby elect Invention I, claims 1 - 11 and 13 - 28, without traverse.

**Species Election**

The Examiner has also required under 35 U.S.C. § 121 that if Applicants elect Invention I, they must also elect one of the following species:

IA. The species of Invention I with a single aperture mask used to form the gate electrode, dielectric, semiconductor, source/drain, and sealing material; or

IB. The species of Invention II with different aperture masks used to form the gate electrode, dielectric, semiconductor, source/drain, and sealing material.

In response, Applicants hereby elect species IB, which is described by claim 28. Applicants assume that this requirement to elect a species applies only to claims 18 – 29. Accordingly, claims 18 – 26, 28 and 29 read on the elected species.

**Concluding Remarks**

Applicants have elected Invention I, species IB. Continued prosecution of this application is respectfully requested.

Respectfully submitted,

Jan. 23, 2008  
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